**Product data sheet** 

## 1. General description

Dual common cathode power Schottky diode designed for high frequency switched mode power supplies in a TO220 plastic package.





## 2. Features and benefits

- High junction temperature up to 175 °C
- Low forward voltage drop, negligible switching losses
- High efficiency

## 3. Applications

- DC to DC converters
- Freewheeling diode
- OR-ing diode
- · Switched mode power supply rectifier

## 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes		Values		Unit
Absolute	maximum rating						
$V_{RRM}$	V <sub>RRM</sub> repetitive peak reverse voltage				200		V
$I_{F(AV)}$	average forward current	$δ$ = 0.5 ; square-wave pulse; $T_{mb}$ ≤ 152 °C; per diode; Fig. 1; Fig. 2; Fig. 3		20			А
$I_{O(AV)}$	average output current	$\delta$ = 0.5 ; square-wave pulse; $T_{mb} \le 150$ °C; both diodes conducting		40			А
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static ch	aracteristics						
$V_{F}$	forward voltage	$I_F = 20 \text{ A}; T_j = 25 \text{ °C}; \text{ per diode}; Fig. 6$		-	0.87	0.92	V
I <sub>R</sub>	reverse current	$V_R = 200 \text{ V}$ ; $T_j = 25 \text{ °C}$ ; per diode; Fig. 7		-	0.1	5	μA

# 5. Pinning information

### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1	mb	
2	K	cathode	<del>                                     </del>	A1 A2
3	A2	anode 2		K Sym125
mb	К	mounting base; connected to cathode		<i>y,</i> 2

# 6. Ordering information

## **Table 3. Ordering information**

Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
WN3S40200CT	TO220	WN3S40200CTQ	Tube	50	SOT78	13-Jun-2008

# 7. Marking

## **Table 4. Marking codes**

Type number	Marking codes
WN3S40200CT	WN3S40 200CT

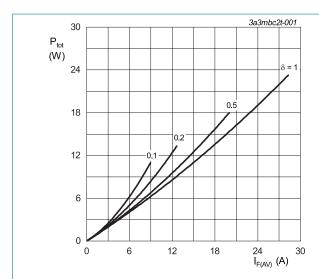
# 8. Limiting values

### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

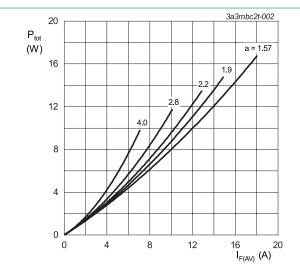
Symbol	Parameter	Conditions	Notes	Values	Unit
$V_{RRM}$	repetitive peak reverse voltage			200	V
$V_{RWM}$	crest working reverse voltage			200	V
$V_R$	reverse voltage	DC		200	V
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5 ; square-wave pulse; T <sub>mb</sub> ≤ 152 °C; per diode; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>		20	А
$I_{O(AV)}$	average output current	$\delta$ = 0.5; square-wave pulse; $T_{mb} \le 150$ °C; both diodes conducting		40	Α
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode; Fig. 4		300	Α
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode		330	Α
T <sub>stg</sub>	storage temperature			-40 to 175	°C
T <sub>j</sub>	junction temperature		[1]	-40 to 175	°C

[1] The heat generated must be less than the thermal conductivity from Junction to Ambient:  $dP_{tot}/dT_j < 1/R_{th(j-a)}$ 



 $I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$ V<sub>o</sub> = 0.635 V; R<sub>s</sub> = 0.0066 Ω

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values; per diode



a = form factor =  $I_{F(RMS)}$  /  $I_{F(AV)}$ V<sub>o</sub> = 0.635 V; R<sub>s</sub> = 0.0066  $\Omega$ 

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values; per diode

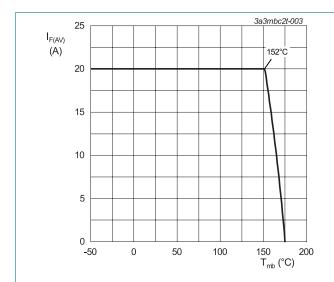


Fig. 3. Average forward current as a function of mounting base temperature; maximum values; per diode

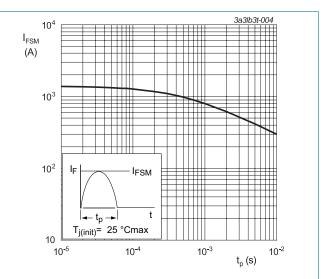


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values; per diode

## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance	per diode; <u>Fig. 5</u>		-	-	1.3	K/W
	from junction to mounting base	both diodes conducting		-	-	0.7	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air	in free air		-	60	-	K/W

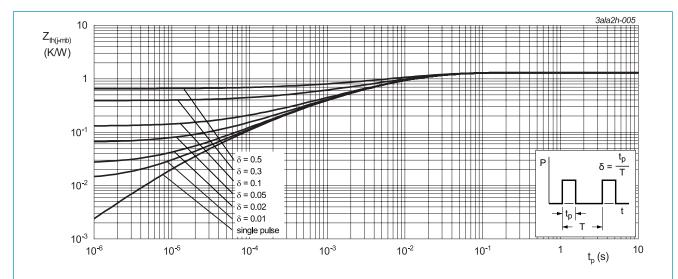
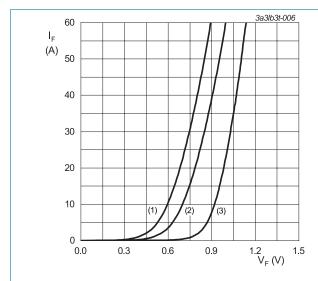


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration; maximum values; per diode

## 10. Characteristics

**Table 7. Characteristics** 

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static ch	aracteristics						
V <sub>F</sub>	forward voltage	$I_F = 20 \text{ A}; T_j = 25 ^{\circ}\text{C}; \text{ per diode}; Fig. 6$		-	0.87	0.92	V
		I <sub>F</sub> = 20 A; T <sub>j</sub> = 125 °C; per diode		-	0.75	-	V
		I <sub>F</sub> = 20 A; T <sub>j</sub> = 175 °C; per diode; <u>Fig. 6</u>		-	0.69	0.74	V
I <sub>R</sub>	reverse current	$V_R = 200 \text{ V; } T_j = 25 \text{ °C; per diode;}$ Fig. 7		-	0.1	5	μΑ
		$V_R = 200 \text{ V}; T_j = 125 ^{\circ}\text{C}; \text{ per diode}; $ Fig. 7		-	0.2	-	mA



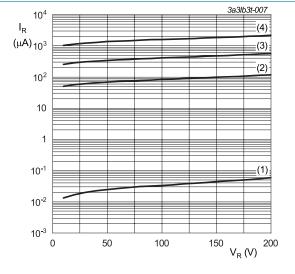
 $V_o$  = 0.635 V;  $R_s$  = 0.0066  $\Omega$ 

(1) T<sub>i</sub> = 175 °C; typical values

(2) T<sub>j</sub> = 175 °C; maximum values

(3)  $T_i = 25$  °C; maximum values

Fig. 6. Forward current as a function of forward voltage; per diode



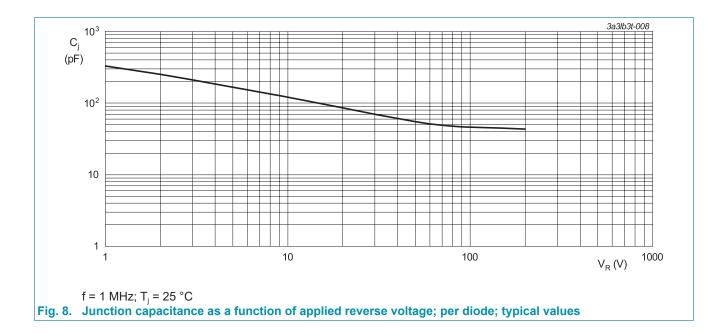
(1)  $T_j = 25$  °C; typical values

(2) T<sub>i</sub> = 125 °C; typical values

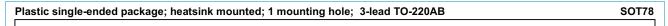
(3) T<sub>j</sub> = 150 °C; typical values

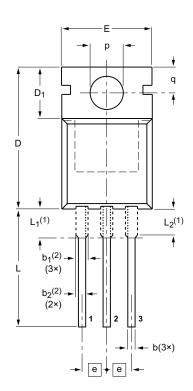
(4) T<sub>i</sub> = 175 °C; typical values

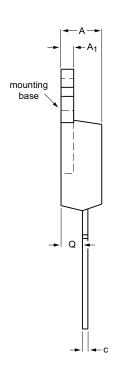
Fig. 7. Reverse leakage current as a function of reverse voltage; per diode; typical values



# 11. Package outline







0 5 10 mm scale

## **DIMENSIONS** (mm are the original dimensions)

UNIT	Α	A <sub>1</sub>	b	b <sub>1</sub> <sup>(2)</sup>	b <sub>2</sub> <sup>(2)</sup>	С	D	D <sub>1</sub>	E	е	L	L <sub>1</sub> <sup>(1)</sup>	L <sub>2</sub> <sup>(1)</sup> max.	р	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

#### Notes

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE	TLINE REFERENCES				EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA		PROJECTION	1330E DATE
SOT78		3-lead TO-220AB	SC-46			<del>08-04-23</del> 08-06-13

## 12. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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